2-input NAND Gate

HITACHI

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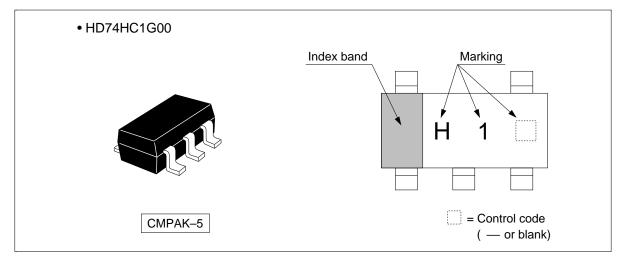
Description

The HD74HC1G00 is high speed CMOS two input NAND gate using silicon gate CMOS process. With CMOS low power dissipation, it provides high speed equivalent to LS–TTL series. The internal circuit of three stages construction with buffer provides wide noise margin and stable output.

Features

- The basic gate function is lined up as hitachi uni logic series.
- Supplied on emboss taping for high speed automatic mounting.
- Electrical characteristics equivalent to the HD74HC00 Supply voltage range : 2 to 6 V Operating temperature range : -40 to +85°C
- $|I_{OH}| = I_{OL} = 2 \text{ mA (min)}$

Outline and Article Indication



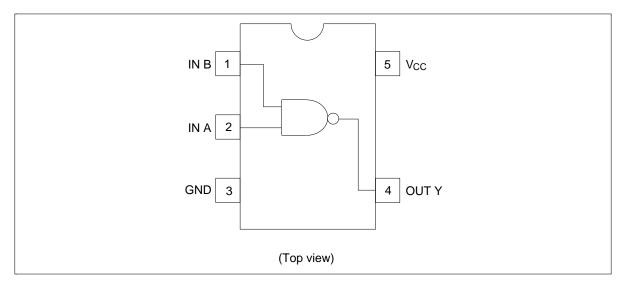


Function Table

Inputs		Output Y				
Α	В					
L	L	Н				
L	Η	Н				
Н	L	Н				
Н	Η	L				
H : High level						

L : Low level

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Test Conditions
Supply voltage range	V _{cc}	–0.5 to 7.0	V	
Input voltage range *1	V	-0.5 to V _{cc} + 0.5	V	
Output voltage range *1, 2	Vo	-0.5 to V _{cc} + 0.5	V	Output : H or L
Input clamp current	I _{IK}	±20	mA	$V_1 < 0 \text{ or } V_1 > V_{cc}$
Output clamp current	I _{ок}	±20	mA	V_{o} < 0 or V_{o} > V_{cc}
Continuous output current	I _o	±25	mA	$V_{o} = 0$ to V_{cc}
$\begin{tabular}{lllllllllllllllllllllllllllllllllll$	$I_{\rm CC}$ or $I_{\rm GND}$	±25	mA	
Maximum power dissipation at Ta = 25° C (in still air) ^{'3}	ι P _τ	200	mW	
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

- 2. This value is limited to 5.5 V maximum.
- 3. The maximum package power dissipation was caluculated using a junction temperature of 150°C.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Test Conditions
Supply voltage range	V _{cc}	2	6	V	
Input voltage range	V	0	V _{cc}	V	
Output voltage range	Vo	0	V _{cc}	V	
Output current	I _{OL}		2.0	mA	$V_{cc} = 4.5 V$
		_	2.6		$V_{cc} = 6.0 V$
	I _{он}		-2.0	mA	$V_{cc} = 4.5 V$
		_	-2.6		$V_{cc} = 6.0 V$
Input rise / fall time	t _r , t _f	0	1000	ns	V _{cc} = 2.0 V
(10% to 90%)		0	500		$V_{cc} = 4.5 V$
		0	400		$V_{cc} = 6.0 V$
Operating temperature	Та	-40	85	°C	

Note: Unused or floating inputs must be held high or low.

Electrical Characteristics

ltem	Symbol	\mathbf{V}_{cc}	$T_a = 25^{\circ}C$			$T_a = -40$ to $85^{\circ}C$		Unit	Test Con	ditions
		(V)	Min	Тур	Max	Min	Max	-		
Input voltage	V _{IH}	2.0	1.5			1.5	_	V		
		4.5	3.15			3.15		_		
		6.0	4.2			4.2		-		
	VIL	2.0			0.5		0.5	_		
		4.5			1.35		1.35	_		
		6.0	_	_	1.8	_	1.8	=		
Output voltage	V _{OH}	2.0	1.9	2.0		1.9		V	V _{IN} =	I _{OH} = -20 μA
		4.5	4.4	4.5		4.4		_	$V_{\mbox{\tiny IH}}$ or $V_{\mbox{\tiny IL}}$	
		6.0	5.9	6.0		5.9	_	_		
		4.5	4.18	4.31		4.13		_		I _{он} = –2 mA
		6.0	5.68	5.80		5.63		-		$I_{OH} = -2.6 \text{ mA}$
	V _{OL}	2.0		0.0	0.1		0.1	_		I _{oL} = 20 μA
		4.5		0.0	0.1		0.1	_		
		6.0		0.0	0.1		0.1	-		
		4.5		0.17	0.26		0.33	_		$I_{OL} = 2 \text{ mA}$
		6.0		0.18	0.26		0.33	-		I _{oL} = 2.6 mA
Input current	I _{IN}	6.0			±0.1		±1.0	μA	$V_{\rm IN} = V_{\rm CC}$ (or GND
Operating current	I _{cc}	6.0			1.0	. <u> </u>	10.0	μA	$V_{\rm IN} = V_{\rm CC}$ (or GND

Switching Characteristics

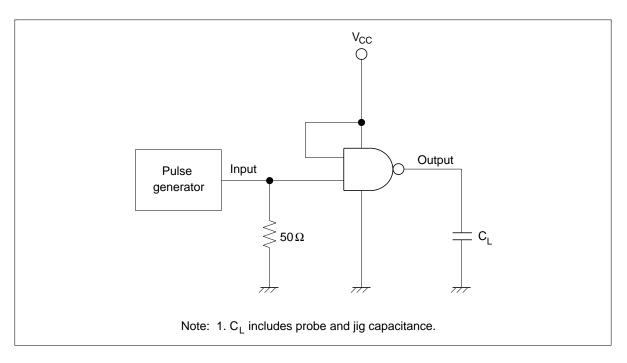
Item	Symbol	$T_a = 25^{\circ}C$					Unit	Test	Conditions
		Min		Тур	Ма	ax	_		
Output rise / fall time	t _{TLH} t _{THL}	_	_		5 10		ns	Test	circuit
Propagation delay time	t _{PLH} t _{PHL}			7 15			ns	Test circuit	
$(C_{L} = 15 \text{ pF}, t_{r} = t_{f} = 6 \text{ ns}$, V _{CC} = 5 V)							
Item	Symbol		T _a = 25°C			T _a = −40 to 85°C		Unit	Test Conditions
		\mathbf{V}_{cc}	Min	Тур	Мах	Min	Max	-	
Output rise / fall time	t _{TLH}	2.0		50	125		155	ns	Test circuit
	t _{⊤⊢∟}	4.5		14	25		31	_	
		6.0		12	21	_	26	-	
Propagation delay time	t _{PLH}	2.0		48	100		125	ns	Test circuit
	t _{PHL}	4.5		12	20		25	_	
		6.0		9	17		21	_	
Input capacitance	C _{IN}	_	_	2.5	5	_	5	pF	
Equivalent capacitance	C _{PD}	_	_	10				pF	

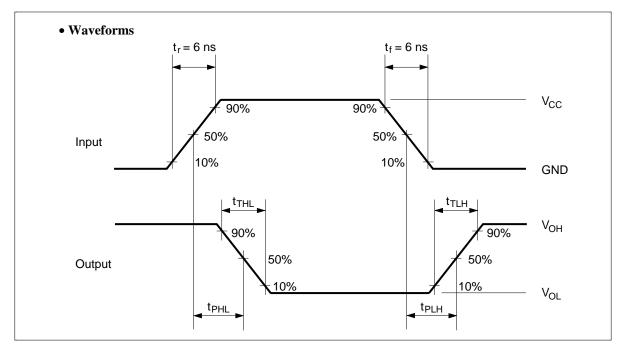
 $(C_{L} = 50 \text{ pF}, t_{r} = t_{f} = 6 \text{ ns})$

Note: C_{PD} is equivalent capacitance inside of the IC calculated from the operating current without load (see test circuit). The average operating current without load is calculated according to the expression below.

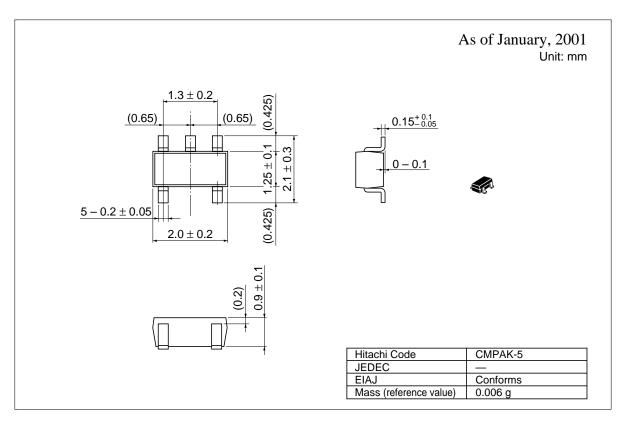
 I_{CC} (opr) = $C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}$

Test Circuit





Package Dimensions



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